



### General Description

- 100% UIS Tested
- Advanced Trench Technology
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

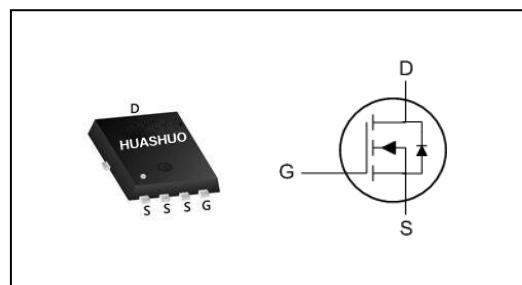
### Product Summary

V <sub>DS</sub>	30	V
R <sub>DS(ON),typ</sub>	1.8	mΩ
I <sub>D</sub>	85	A

### Applications

- Power Management in Desktop Computer
- DC/DC Converters

### PRPAK5X6 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>c</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sub>1,6</sub>	85	A
I <sub>D</sub> @T <sub>c</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sub>1,6</sub>	67	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	250	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	151	mJ
I <sub>AS</sub>	Avalanche Current	55	A
P <sub>D</sub> @T <sub>c</sub> =25°C	Total Power Dissipation <sup>4</sup>	48	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	50	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	2.6	°C/W



**N-Ch 30V Fast Switching MOSFETs**

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30	---	---	V
R <sub>DSON</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =20A	---	1.8	2.2	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =20A	---	2.5	3.6	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.6	2.2	V
I <sub>bss</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C	---	---	5	
I <sub>GS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fS</sub>	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =20A	---	91	---	S
R <sub>G</sub>	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz	---	1.7	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =15V , V <sub>GS</sub> =10V , I <sub>D</sub> =20A	---	21	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	12.5	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	14.5	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V , R <sub>G</sub> =3.3Ω, I <sub>D</sub> =20A	---	12	---	ns
T <sub>r</sub>	Rise Time		---	6	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	38.5	---	
T <sub>f</sub>	Fall Time		---	11.5	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz	---	3032	---	pF
C <sub>oss</sub>	Output Capacitance		---	1588	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	207	---	

**Diode Characteristics**

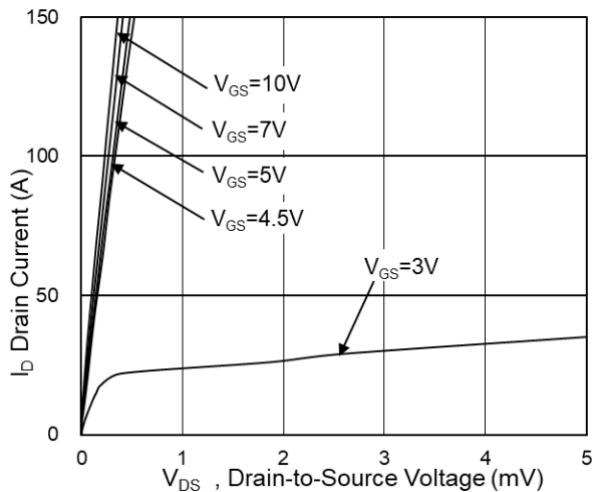
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>s</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	85	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>s</sub> =1A , T <sub>J</sub> =25°C	---	---	1.2	V

Note :

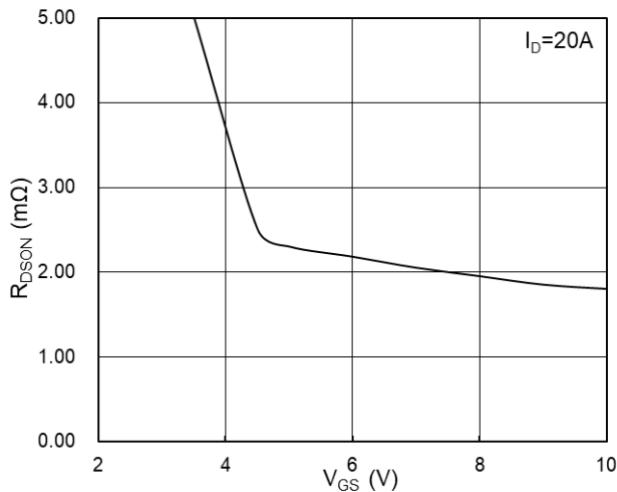
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=55A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.
- 6.Package limitation current is 85A.



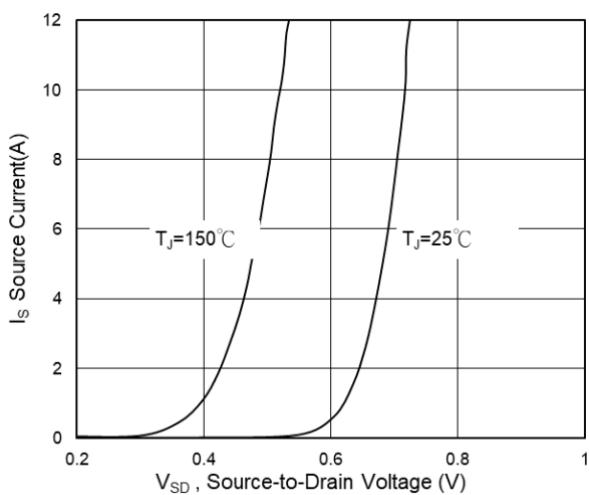
### Typical Characteristics



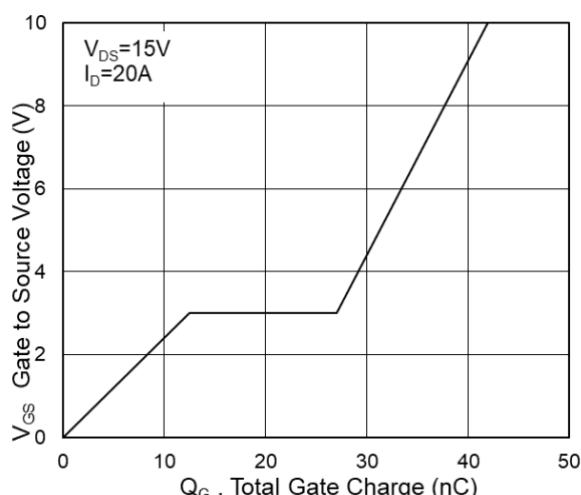
**Fig.1 Typical Output Characteristics**



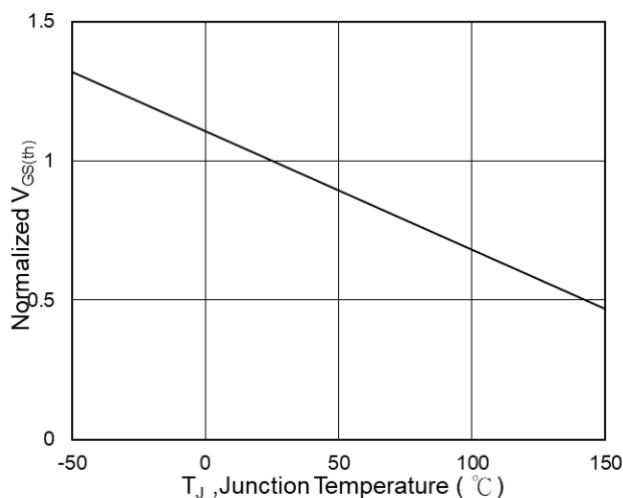
**Fig.2 On-Resistance vs G-S Voltage**



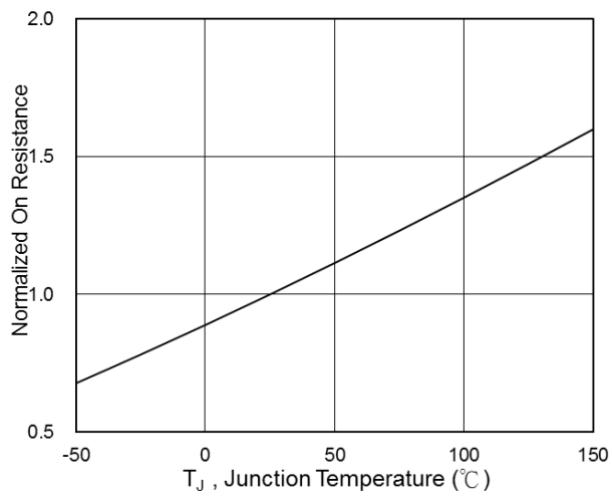
**Fig.3 Source Drain Forward Characteristics**



**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$**



**Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$**



N-Ch 30V Fast Switching MOSFETs

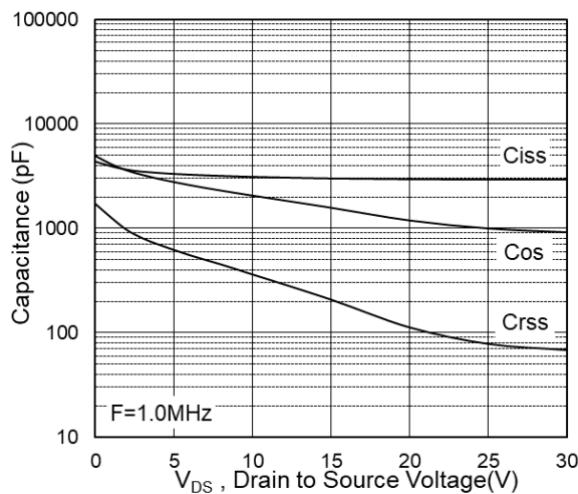


Fig.7 Capacitance

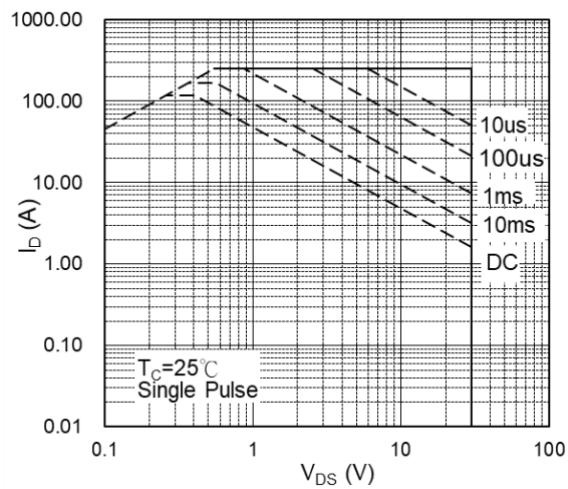


Fig.8 Safe Operating Area

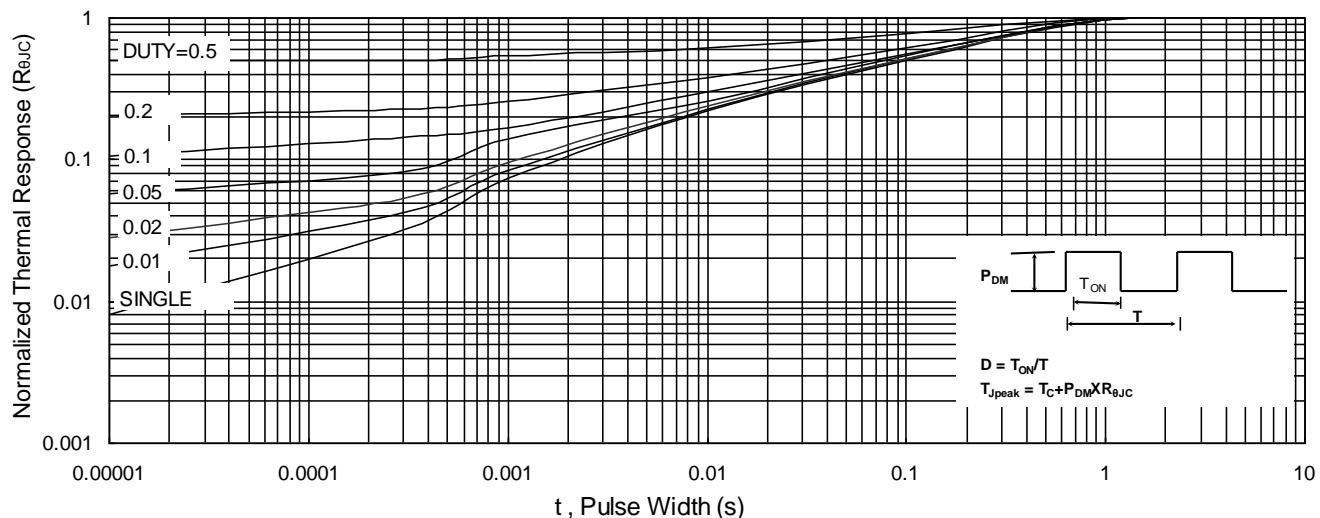


Fig.9 Normalized Maximum Transient Thermal Impedance

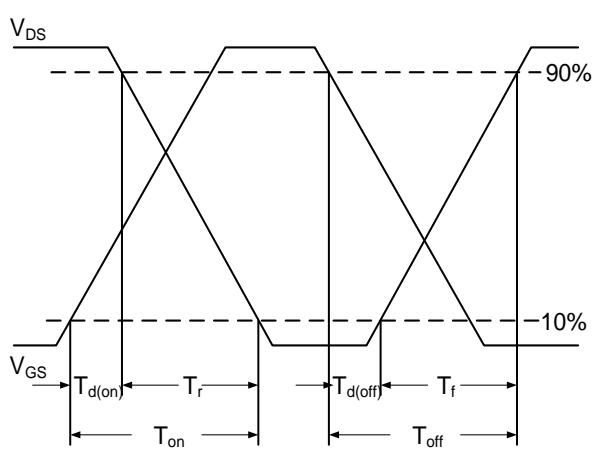


Fig.10 Switching Time Waveform

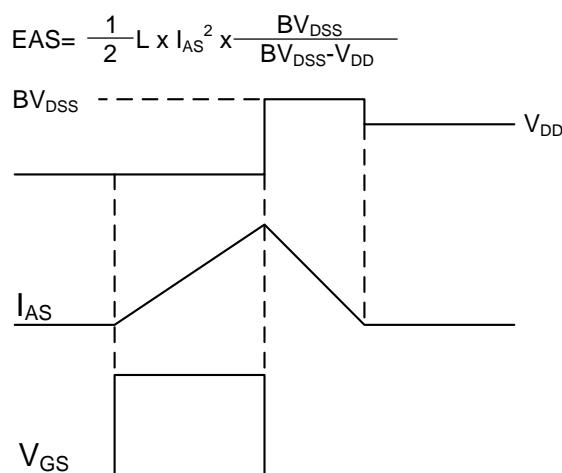
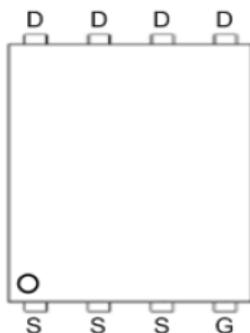
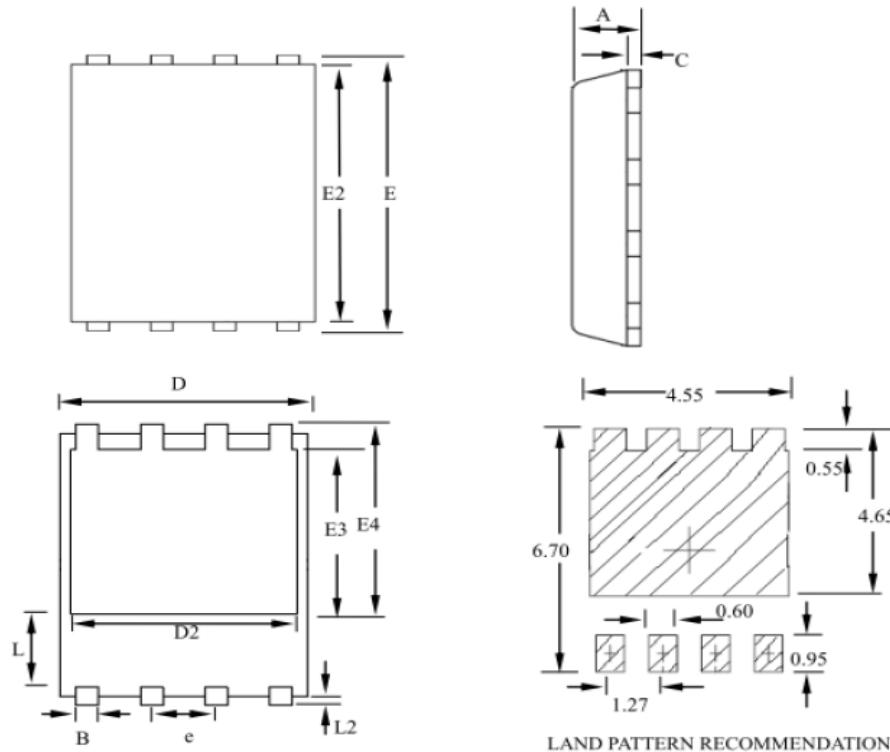


Fig.11 Unclamped Inductive Switching



## Ordering Information

Part Number	Package code	Packaging
HSBA3094	PRPAK5*6	3000/Tape&Reel



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
B	0.30	--	0.51	0.012	--	0.020
C	0.15	--	0.35	0.006	--	0.014
D	4.80	--	5.30	0.189	--	0.209
D2	3.61	--	4.35	0.142	--	0.171
E	5.90	--	6.35	0.232	--	0.250
E2	5.42	--	5.90	0.213	--	0.232
E3	3.23	--	3.90	0.127	--	0.154
E4	3.69	--	4.55	0.145	--	0.179
L	0.61	--	1.80	0.024	--	0.071
L2	0.05	--	0.36	0.002	--	0.014
e	--	1.27	--	--	0.050	--